

|              |         |   |
|--------------|---------|---|
| <b>SANYO</b> | No.2953 | <b>DD20R</b>  |
|              |         | Diffused Junction Type Silicon Diode<br>Damper Diode for<br>Very High-Definition Display Applications |

**Features**

- High breakdown voltage ( $V_{RRM} : -1500V$ )
- High reliability
- One-point fixing type plastic molded package facilitating easy mounting and heat dissipation
- Fast forward/reverse recovery time

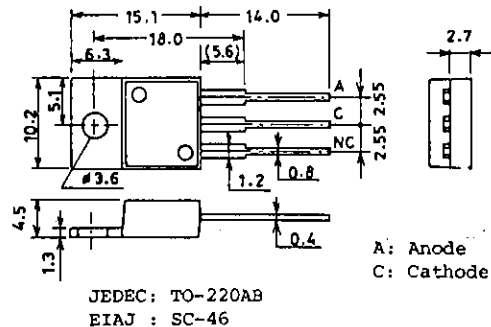
**Absolute Maximum Ratings at  $T_a = 25^\circ C$**

|                                    |           |                                    | unit       |
|------------------------------------|-----------|------------------------------------|------------|
| Repetitive Peak Reverse Voltage    | $V_{RRM}$ | -1500                              | V          |
| Nonrepetitive Peak Reverse Voltage | $V_{RSM}$ | -1500                              | V          |
| Average Output Current             | $I_O$     | 2                                  | A          |
| Peak Output Current                | $i_{op}$  | $PW \leq 100\mu s, duty \leq 50\%$ | A          |
| Surge Forward Current              | $I_{FSM}$ | Sine wave 10ms                     | A          |
| Junction Temperature               | $T_j$     | 150                                | $^\circ C$ |
| Storage Temperature                | $T_{stg}$ | -55 to +150                        | $^\circ C$ |

**Electrical Characteristics at  $T_a = 25^\circ C$**

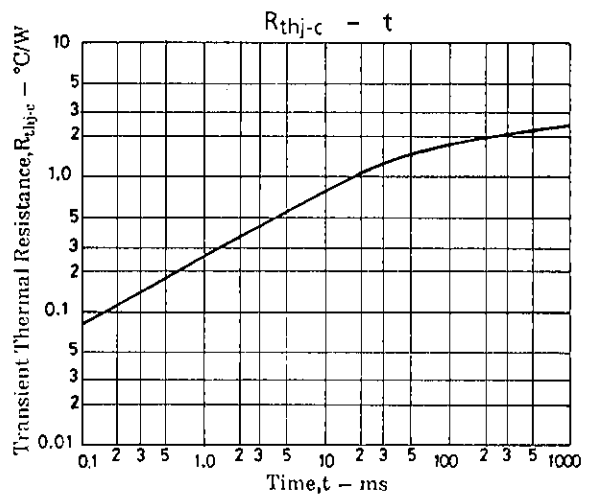
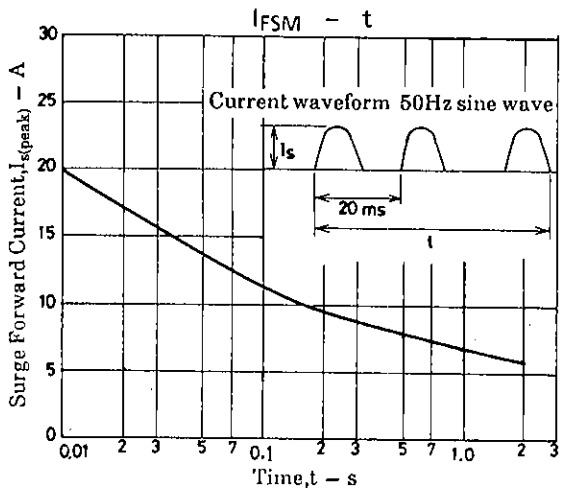
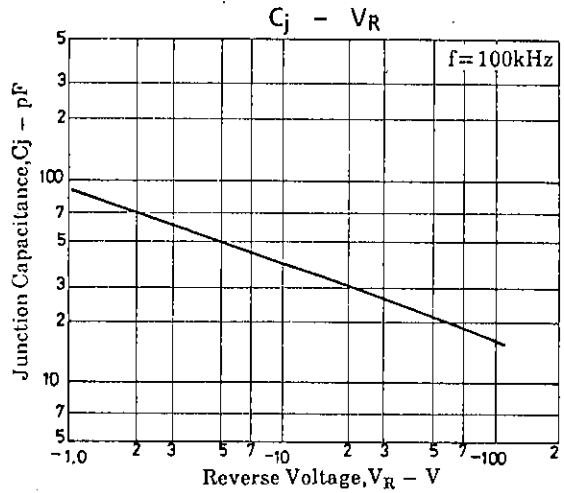
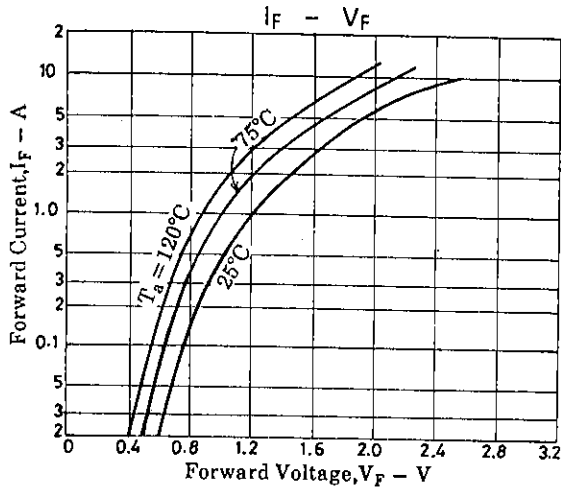
|                       |             |                          | min   | typ | max  | unit         |
|-----------------------|-------------|--------------------------|-------|-----|------|--------------|
| Reverse Voltage       | $V_R$       | $I_R = -1mA$             | -1500 |     |      | V            |
| Forward Voltage       | $V_F$       | $I_F = 2A$               |       |     | 2    | V            |
| Reverse Current       | $I_R$       | $V_R = -1000V$           |       |     | -200 | $\mu A$      |
| Reverse Recovery Time | $t_{rr}$    | $I_F = -I_R = 100mA$     |       |     | 1    | $\mu s$      |
| Forward Recovery Time | $t_{fr}$    | $I_F = 100mA$            | 0.1   | 0.2 |      | $\mu s$      |
| Junction Capacitance  | $C_j$       | $V_R = -10V, f = 100kHz$ | 40    |     |      | pF           |
| Thermal Resistance    | $R_{thj-c}$ | Junction-Case            |       |     | 2.5  | $^\circ C/W$ |

**Package Dimensions 1211A**  
( unit: mm )



A: Anode  
C: Cathode

# DD20R



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